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The mechanism of electroforming of metal oxide memristive switches

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#	Paper	IF	Citations
646	Microscopic origin of bipolar resistive switching of nanoscale titanium oxide thin films. <i>Applied Physics Letters</i> , 2009 , 95, 162108	3.4	97
645	Electrical transport and thermometry of electroformed titanium dioxide memristive switches. 2009 , 106, 124504		81
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